

<p>NPN型 低频放大 小功率 贴片三极管 NPN Plastic-Encapsulate Transistors SMD</p>	<p><b>MMBT2222A</b> 对应其他工业型号 <b>2222A</b></p>
<ul style="list-style-type: none"> <li>■ High breakdown voltage</li> <li>■ Low collector-emitter saturation voltage</li> <li>■ Transistor Polarity: NPN</li> <li>■ Transistor pinout: BEC</li> <li>■ SOT-23 Package</li> <li>■ Marking Code: 1P</li> </ul>	

<p style="text-align: center;">Inner circuit</p>  <p style="text-align: center;">SOT-23 内部结构</p>	<p style="text-align: center;">MMBT2222A</p>  <p style="text-align: center;">SOT-23 管脚排列</p>	<p style="text-align: center;">元件标识 (打印)</p>  <p style="text-align: center;">DEVICE MARKING</p>
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**CLASSIFICATION OF hFE**

RANK	L	H
RANGE	100~200	200~300

**MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
<b>V<sub>CB0</sub></b>	Collector-Base Voltage	75	V
<b>V<sub>CEO</sub></b>	Collector-Emitter Voltage	40	V
<b>V<sub>EBO</sub></b>	Emitter-Base Voltage	6	V
<b>I<sub>C</sub></b>	Collector Current -Continuous	600	mA
<b>P<sub>C</sub></b>	Collector Dissipation	300	mW
<b>R<sub>θJA</sub></b>	Thermal Resistance, Junction to Ambient	417	°C/W
<b>T<sub>J</sub>,T<sub>stg</sub></b>	Operation Junction and Storage Temperature Range	-55~+150	°C

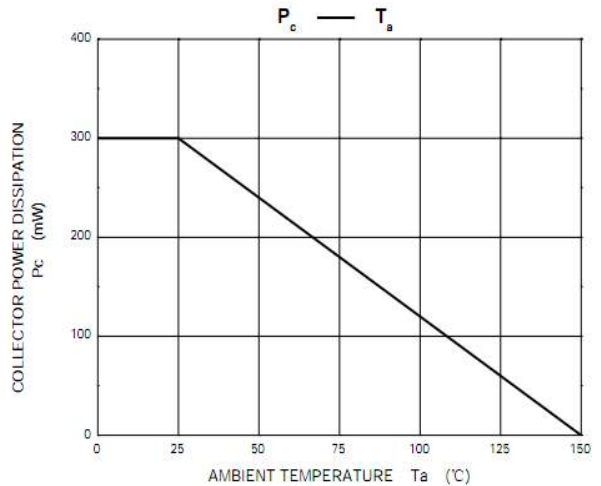
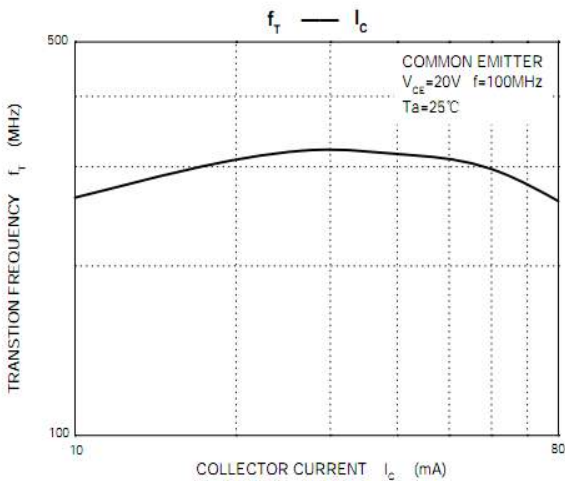
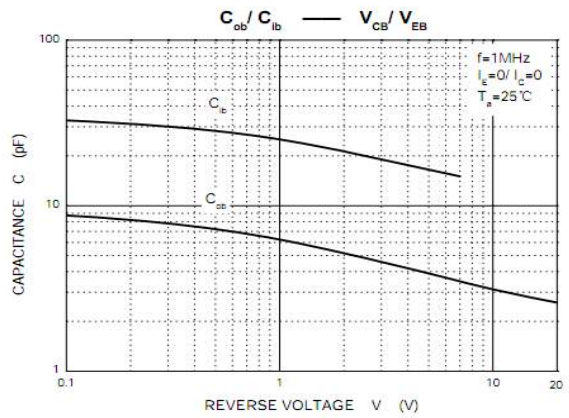
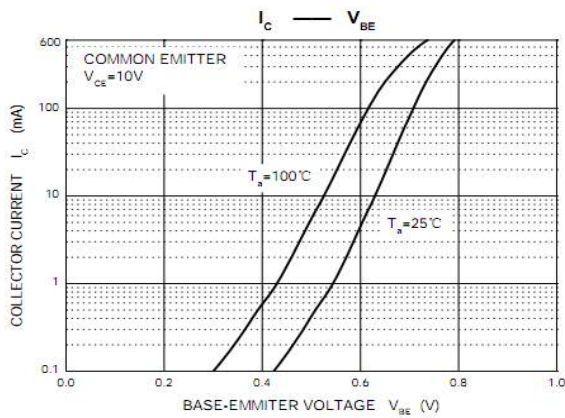
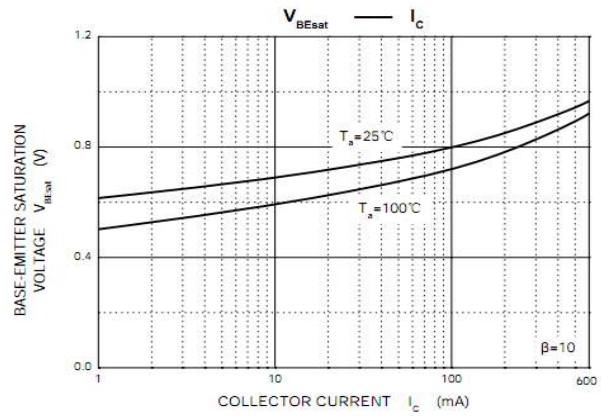
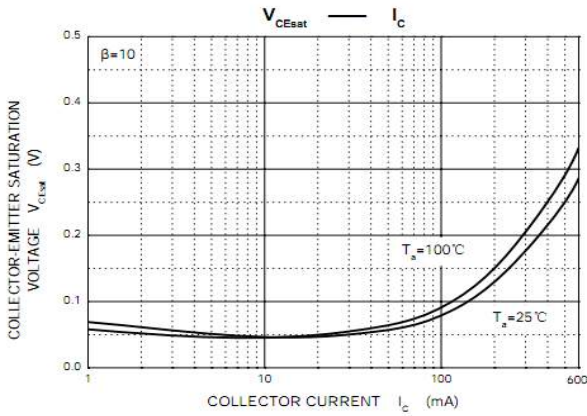
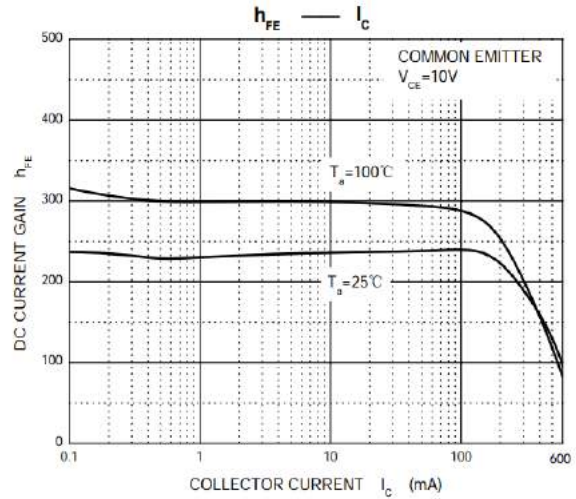
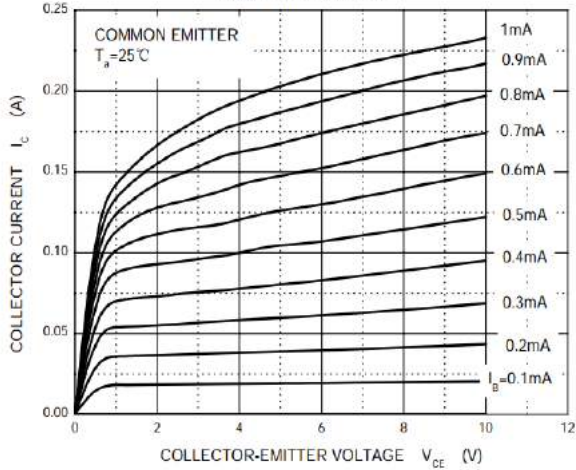
**■ ELECTRICAL CHARACTERISTICS ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	75			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	$I_C=10\text{mA}, I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=60\text{V}, I_E=0$			0.01	$\mu\text{A}$
Collector cut-off current	$I_{CEX}$	$V_{CE}=30\text{V}, V_{BE(off)}=3\text{V}$			0.01	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=3\text{V}, I_C=0$			0.1	$\mu\text{A}$
DC current gain	$h_{FE(1)}^*$	$V_{CE}=10\text{V}, I_C=150\text{mA}$	100		300	
	$h_{FE(2)}$	$V_{CE}=10\text{V}, I_C=0.1\text{mA}$	40			
	$h_{FE(3)}^*$	$V_{CE}=10\text{V}, I_C=500\text{mA}$	42			
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	$I_C=500\text{mA}, I_B=50\text{mA}$ $I_C=150\text{mA}, I_B=15\text{mA}$			1 0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}^*$	$I_C=500\text{mA}, I_B=50\text{mA}$ $I_C=150\text{mA}, I_B=15\text{mA}$			2.0 1.2	V
Transition frequency	$f_T$	$V_{CE}=20\text{V}, I_C=20\text{mA},$ $f=100\text{MHz}$	300			MHz
Delay time	$t_d$	$V_{CC}=30\text{V}, V_{BE(off)}=-0.5\text{V}$			10	ns
Rise time	$t_r$	$I_C=150\text{mA}, I_{B1}=15\text{mA}$			25	ns
Storage time	$t_s$	$V_{CC}=30\text{V}, I_C=150\text{mA}$			225	ns
Fall time	$t_f$	$I_{B1}=-I_{B2}=15\text{mA}$			60	ns

\*pulse test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

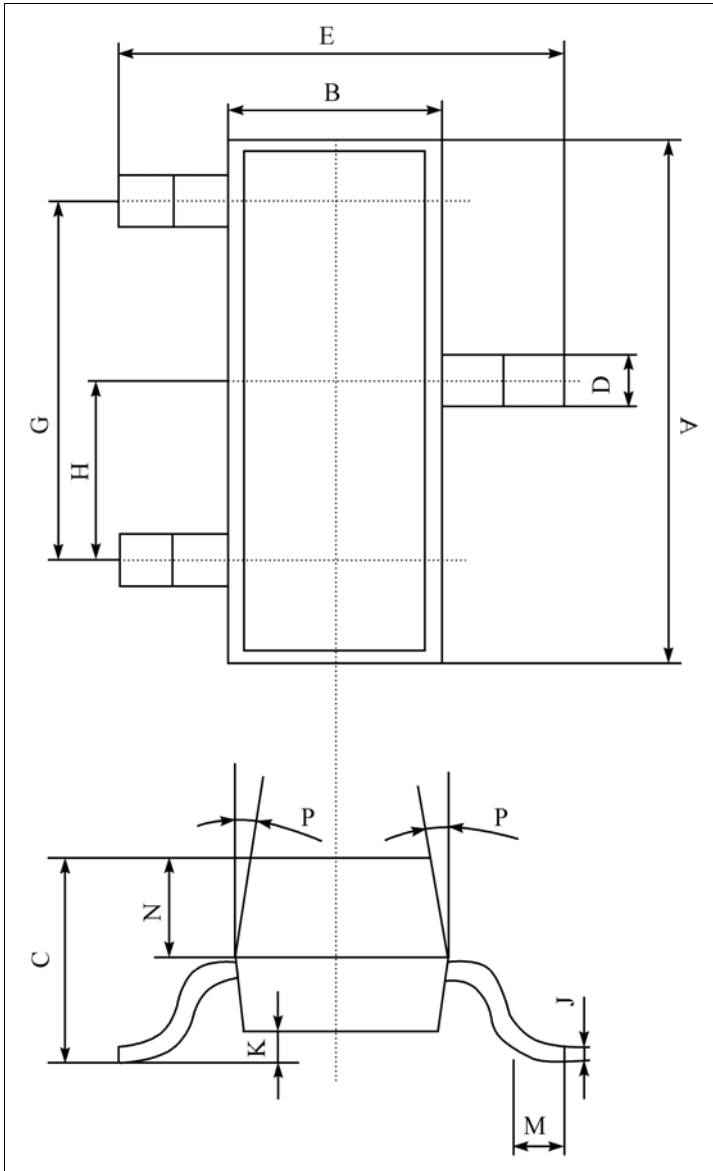
### TYPICAL CHARACTERISTICS

Static Characteristic



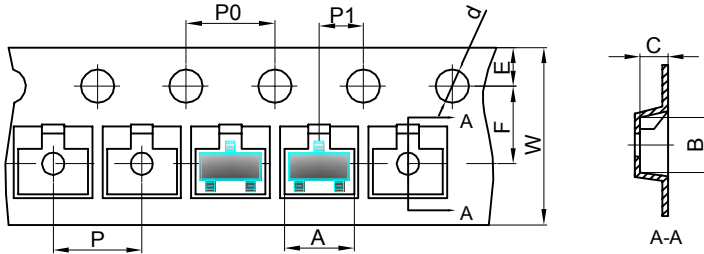
**■ DIMENSION**

单位 (UNIT) : mm

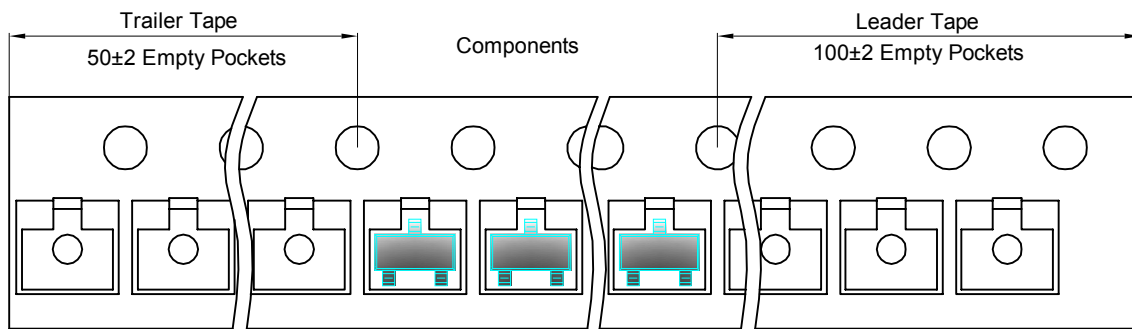
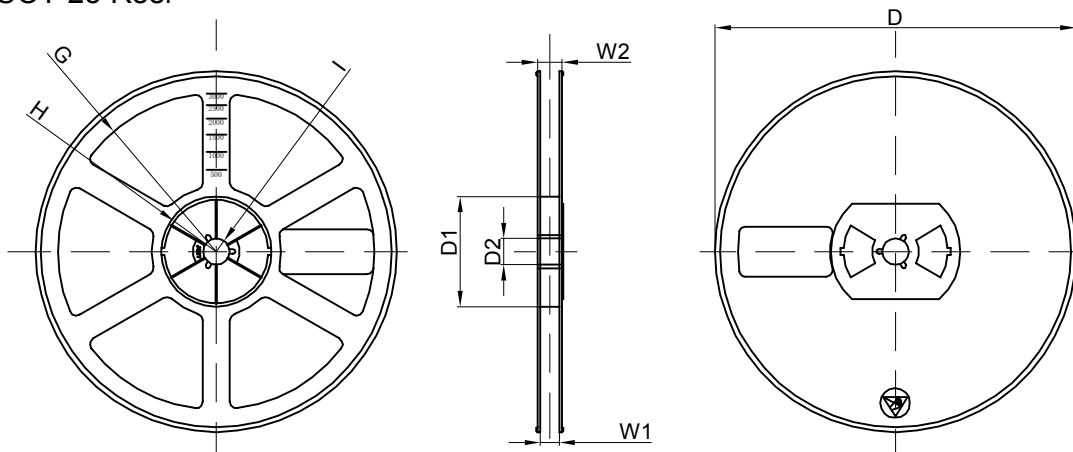


序号	数值及公差
A	2.90±0.10
B	1.30±0.10
C	1.00±0.10
D	0.40±0.10
E	2.40±0.20
G	1.90±0.10
H	0.95±0.05
J	0.13±0.05
K	0.00-0.10
M	≥0.20
N	0.60±0.10
P	7±2°

**Packing**  
 SOT-23 包装规格  
 SMD片式表面贴封装  
 包装方式: 载带卷盘包装  
**Tape & Reel, 3Kpcs/Reel**  
 每卷数量3000只 (3Kpcs/Reel)  
 每盒数量45000只 (45Kpcs/BOX)  
 每箱数量180000只 (180Kpcs/Cartons)

**SOT-23 Embossed Carrier Tape**


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

**SOT-23 Tape Leader and Trailer**

**SOT-23 Reel**


Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	45,000 pcs	192×192×193	180,000 pcs	404×404×214	